

programmed to a resistance state, at least a portion of the material being programmable to a desired data state.

15. The apparatus of claim **14**, wherein the desired data state is achieved by programming at least the portion of the material to a corresponding resistance state.

16. The apparatus of claim **15**, wherein the material is configured to be changed in response to a signal to have a different resistance state.

17. The apparatus of claim **11**, further comprising an access component coupled to each of the plurality of RCM cells to allow access to a respective one of the plurality of RCM cells to read information from or to write information to the respective memory cell.

18. The apparatus of claim **17**, wherein the access component comprises a transistor coupled to and activated by signals on access lines, the access lines being coupled to the plurality of RCM cells.

19. The apparatus of claim **17**, wherein the access component comprises a diode coupled to access lines, the access lines being coupled to the plurality of RCM cells.

20. A system, comprising:

a first region including a first plurality of resistance change memory (RCM) cells;

a second region having a second plurality of RCM cells; and

drive circuitry electrically coupled to each of the first plurality of RCM cells and the second plurality of RCM cells to selectively provide one of a plurality of signal pulse types to selected ones of the plurality of RCM cells, each of the plurality of signal pulse types having a different attribute and corresponding to a different memory function type.

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